

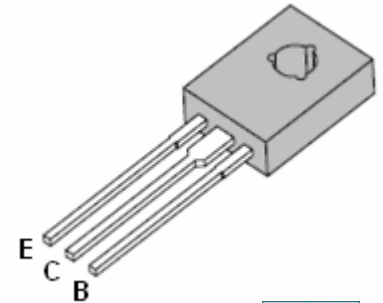
Plastic NPN Epitaxial Silicon Power Transistor

Features

- High collector-emitter breakdown voltage
- Suitable for high voltage general purpose applications
- Complement to MJE350

Mechanical Data

Case:	TO-126, Plastic Package
Terminals:	Solderable per MIL-STD-202, Method 208
Weight:	0.08 ounces, 2.24 grams



TO-126



Absolute Maximum Ratings ($T_{Ambient}=25^{\circ}C$ unless noted otherwise)

Symbol	Description	Value	Unit
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	3	V
I_C	Collector Current Continuous	0.5	A
P_D	Power Dissipation @ $T_a=25^{\circ}C$ Derate above $25^{\circ}C$	1.25 10	W mW/ $^{\circ}C$
	Power Dissipation @ $T_c=25^{\circ}C$ Derate above $25^{\circ}C$	20 0.16	W W/ $^{\circ}C$
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-65 ~ +150	$^{\circ}C$

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Thermal Characteristics

Symbol	Description	Value	Unit
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient in Free Air	100	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance from Junction to Case	6.25	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics ($T_{\text{Ambient}}=25^{\circ}\text{C}$ unless noted otherwise)

Symbol	Description	Conditions	Min.	Max.	Unit
$V_{CE(sus)}$	Collector-Emitter Sustaining Voltage	$I_C=1\text{mA}$, $I_B=0$	300	-	V
I_{CBO}	Collector-Base Cut-off Current	$V_{CB}=300\text{V}$, $I_E=0$	-	100	μA
I_{EBO}	Emitter-Base Cut-off Current	$V_{EB}=3\text{V}$, $I_C=0$	-	100	μA
h_{FE}	DC Current Gain	$V_{CE}=10\text{V}$, $I_C=50\text{mA}$	30	240	

Typical Characteristics Curves

Fig.1- DC Current Gain

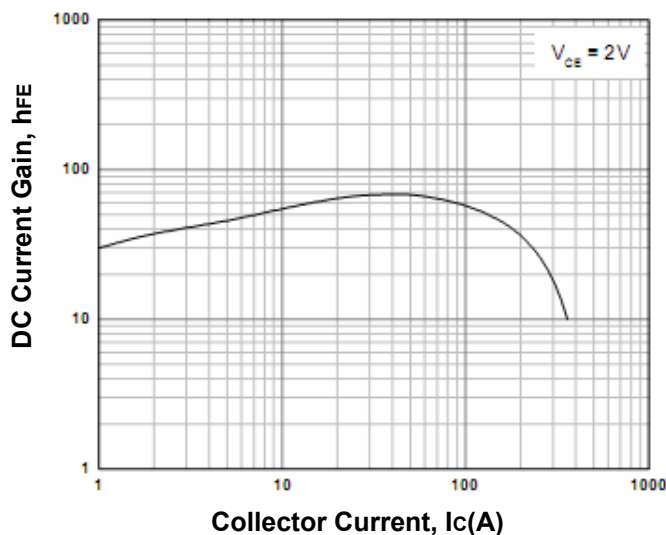
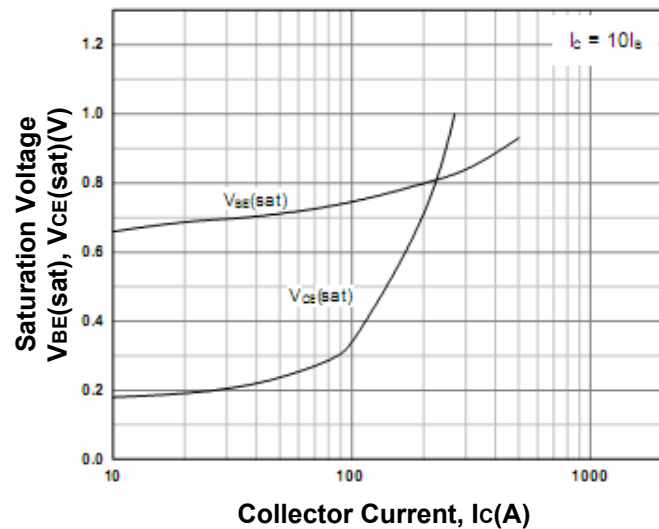


Fig.2- Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



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Fig.3- Safe Operating Area

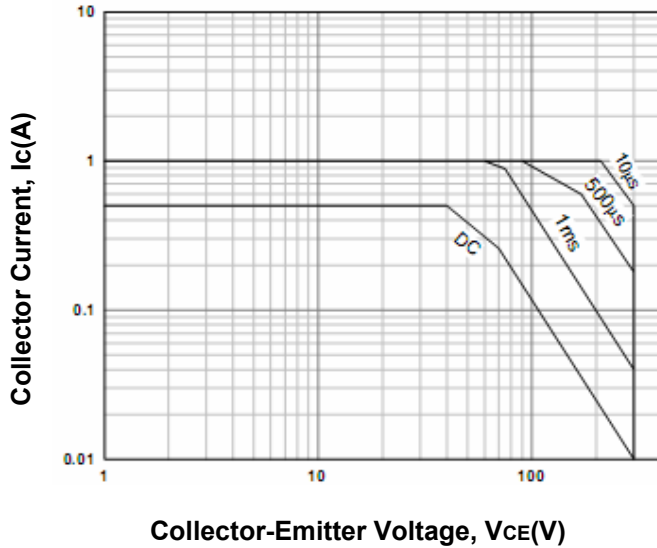
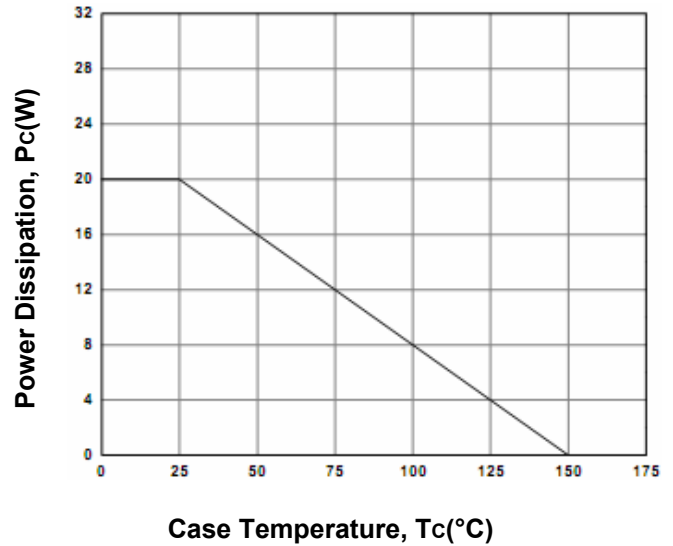
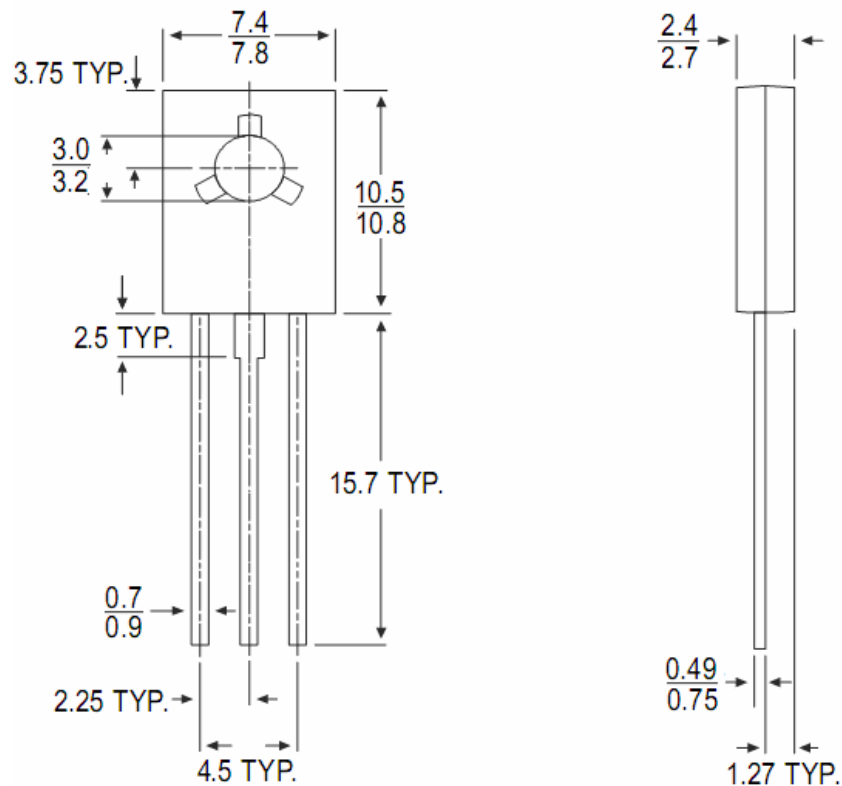


Fig.4- Power Derating



Dimensions in mm



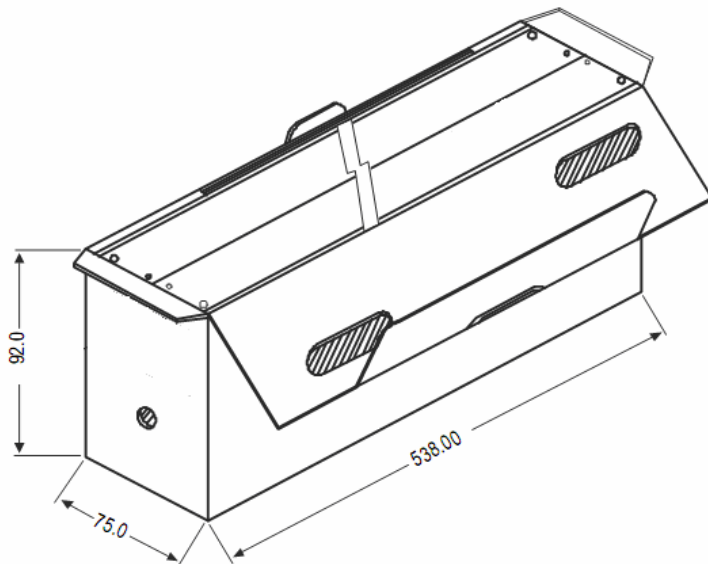
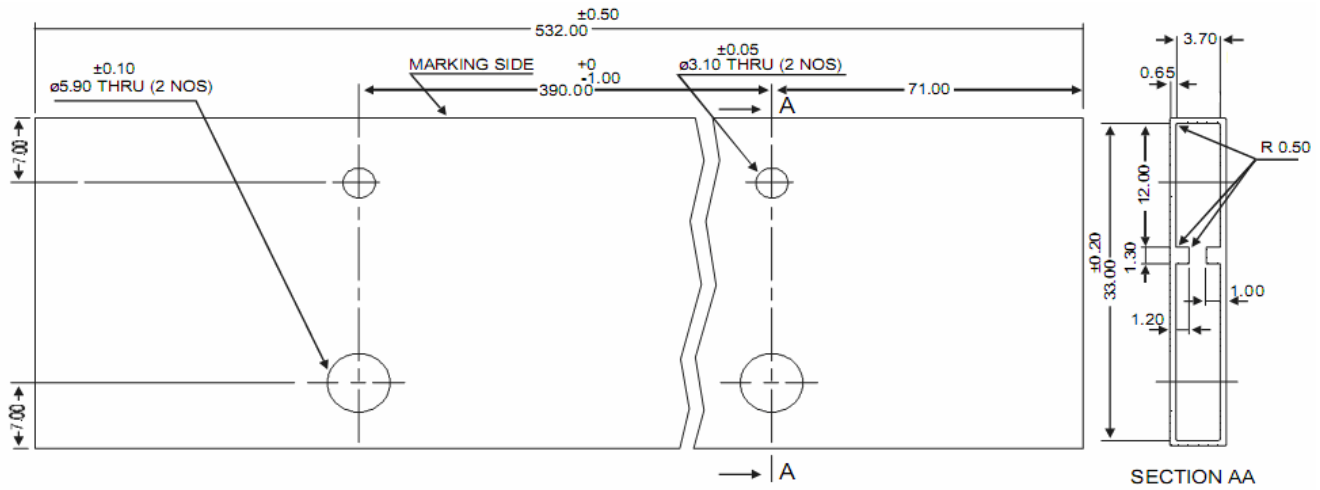
TO-126

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Packing Information

Tube Dimensions



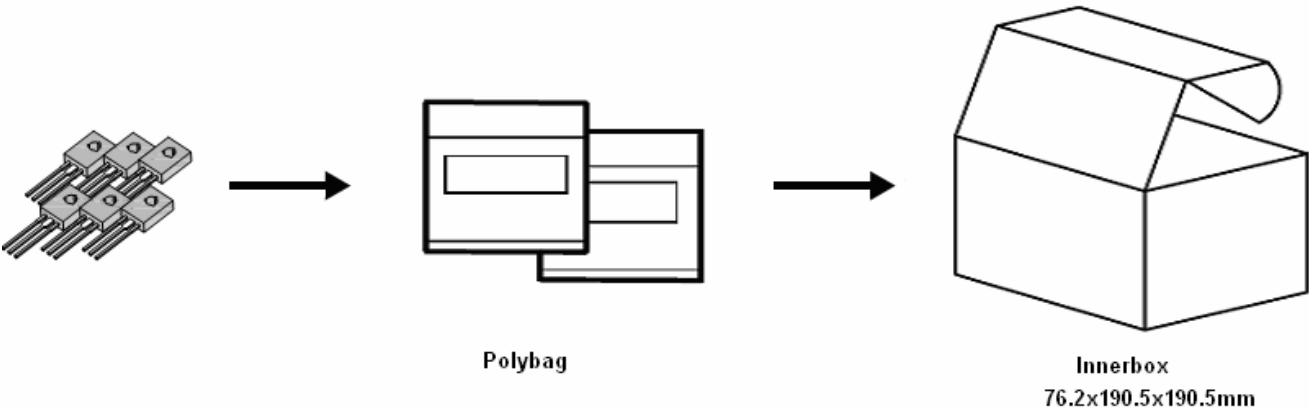
GENERAL TOLERANCE					
0 mm	0.01 mm	30.01 mm	120.01 mm	ABOVE	ANGULAR
5 mm	30 mm	120 mm	315 mm	315 mm	
±0.1	±0.2	±0.3	±0.5	±0.8	±0° 30"

All dimensions in mm

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Bulk Dimensions



Packing Details

Pack	Description	Standard Pack	Inner Box	Carton Box
BL	Bulk, RoHS	500/polybag	2K	32K
TU	Tube, RoHS	50/tube	1K	10K

How to contact us:

US HEADQUARTERS

28040 WEST HARRISON PARKWAY, VALENCIA, CA 91355-4162

Tel: (800) TAITRON (800) 824-8766 (661) 257-6060

Fax: (800) TAITFAX (800) 824-8329 (661) 257-6415

Email: taitron@taitroncomponents.com

Http://www.taitroncomponents.com

TAITRON COMPONENTS MEXICO, S.A .DE C.V.

BOULEVARD CENTRAL 5000 INTERIOR 5 PARQUE INDUSTRIAL ATITALAQUIA, HIDALGO C.P.

42970 MEXICO

Tel: +52-55-5560-1519

Fax: +52-55-5560-2190

TAITRON COMPONENTS INCORPORATED REPRESENTAÇÕES DO BRASIL LTDA

RUA DOMINGOS DE MORAIS, 2777, 2.ANDAR, SALA 24 SAÚDE - SÃO PAULO-SP 04035-001 BRAZIL

Tel: +55-11-5574-7949

Fax: +55-11-5572-0052

TAITRON COMPONENTS INCORPORATED, SHANGHAI REPRESENTATIVE OFFICE

METROBANK PLAZA, 1160 WEST YAN' AN ROAD, SUITE 1503, SHANGHAI, 200052, CHINA

Tel: +86-21-5424-9942

Fax: +86-21-5424-9931